High speed 1200 V TRENCHSTOP™ IGBT 7 Technology co-packed with full rated current, soft-commutating, ultra-fast recovery and low Qrr emitter controlled 7 Rapid diode

Features

- V_{CE} = 1200 V
- I_C = 50 A
- Maximum junction temperature T_{vjmax} = 175°C
- Best-in-class high speed IGBT co-packed with full rated current, low Q_{rr} and soft-commutating high speed diode
- Low saturation voltage V_{CEsat} = 1.7 V at T_{vj} = 25°C
- Optimized for high efficiency in high speed hard switching topologies (2-L inverter, 3-L NPC T-type, ...)
- Easy paralleling capability due to positive temperature coefficient in V_{CEsat}
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models: http://www.infineon.com/igbt/

Halogen-free
Lead-free
Green
RoHS

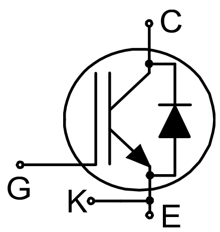
Potential applications

- Industrial UPS
- EV-Charging
- String inverter
- Welding

Product validation

- Qualified for industrial applications according to the relevant tests of JEDEC47/20/22

Description



Type	Package	Marking
IKZA50N120CH7	PG-TO247-4-STD-NT3.7	K50MCH7

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1 Package

Table 1 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Internal emitter inductance measured 5 mm (0.197 in.) from case	L_E			13		nH
Storage temperature	T_{stg}		-55		150	°C
Soldering temperature	T_{sold}	wave soldering 1.6 mm (0.063 in.) from case for 10 s			260	°C
Mounting torque	M	M3 screw, Maximum of mounting processes: 3			0.6	Nm
Thermal resistance, junction-ambient	$R_{th(j-a)}$				40	K/W
IGBT thermal resistance, junction-case	$R_{th(j-c)}$			0.29	0.38	K/W
Diode thermal resistance, junction-case	$R_{th(j-c)}$			0.5	0.65	K/W

2 IGBT

Table 2 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CE}	$T_{vj} \geq 25$ °C		1200	V
DC collector current, limited by T_{vjmax}	I_C	limited by bondwire	$T_c = 25$ °C	100	A
			$T_c = 100$ °C	82	
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpulse}			200	A
Turn-off safe operating area		$V_{CC} \leq 800$ V, $V_{CE,peak} < 1200$ V, $V_{GE} = 0/15$ V, $R_{Goff} \geq 23\ \Omega$, $T_{vj} \leq 175$ °C		200	A
Gate-emitter voltage	V_{GE}			±20	V
Transient gate-emitter voltage	V_{GE}	$t_p \leq 0.5$ µs, $D < 0.001$		±25	V
Power dissipation	P_{tot}		$T_c = 25$ °C	398	W
			$T_c = 100$ °C	199	

Table 3 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	V_{CEsat}	I_C = 50 A, V_{GE} = 15 V	T_{vj} = 25 °C		1.7	2.15	V
			T_{vj} = 175 °C		2		
Gate-emitter threshold voltage	V_{GEth}	I_C = 0.8 mA, V_{CE} = V_{GE}		4.7	5.5	6.2	V
Zero gate-voltage collector current	I_{CES}	V_{CE} = 1200 V, V_{GE} = 0 V	T_{vj} = 25 °C			40	µA
			T_{vj} = 175 °C		3500		
Gate-emitter leakage current	I_{GES}	V_{CE} = 0 V, V_{GE} = 20 V				100	nA
Transconductance	g_{fs}	I_C = 50 A, V_{CE} = 20 V			98		S
Input capacitance	C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V, f = 100 kHz			6.7		nF
Output capacitance	C_{oes}	V_{CE} = 25 V, V_{GE} = 0 V, f = 100 kHz			134		pF
Reverse transfer capacitance	C_{res}	V_{CE} = 25 V, V_{GE} = 0 V, f = 100 kHz			38		pF
Gate charge	Q_G	I_C = 50 A, V_{GE} = 15 V, V_{CC} = 960 V			372		nC
Turn-on delay time	$t_{d(on)}$	V_{CC} = 600 V, V_{GE} = 0/15 V, $R_{G(on)}$ = 8 Ω, $R_{G(off)}$ = 8 Ω	T_{vj} = 25 °C, I_C = 50 A		39		ns
			T_{vj} = 175 °C, I_C = 50 A		36		
Rise time (inductive load)	t_r	V_{CC} = 600 V, V_{GE} = 0/15 V, $R_{G(on)}$ = 8 Ω, $R_{G(off)}$ = 8 Ω	T_{vj} = 25 °C, I_C = 50 A		13		ns
			T_{vj} = 175 °C, I_C = 50 A		15		
Turn-off delay time	$t_{d(off)}$	V_{CC} = 600 V, V_{GE} = 0/15 V, $R_{G(on)}$ = 8 Ω, $R_{G(off)}$ = 8 Ω	T_{vj} = 25 °C, I_C = 50 A		333		ns
			T_{vj} = 175 °C, I_C = 50 A		411		
Fall time (inductive load)	t_f	V_{CC} = 600 V, V_{GE} = 0/15 V, $R_{G(on)}$ = 8 Ω, $R_{G(off)}$ = 8 Ω	T_{vj} = 25 °C, I_C = 50 A		50		ns
			T_{vj} = 175 °C, I_C = 50 A		143		
Turn-on energy	E_{on}	V_{CC} = 600 V, V_{GE} = 0/15 V, $R_{G(on)}$ = 8 Ω, $R_{G(off)}$ = 8 Ω	T_{vj} = 25 °C, I_C = 50 A		1.05		mJ
			T_{vj} = 175 °C, I_C = 50 A		1.62		

(table continues...)

Table 3 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Turn-off energy	E_{off}	V_{CC} = 600 V, V_{GE} = 0/15 V, $R_{G(on)}$ = 8 Ω, $R_{G(off)}$ = 8 Ω	T_{vj} = 25 °C, I_C = 50 A		1.4		mJ
			T_{vj} = 175 °C, I_C = 50 A		2.96		
Total switching energy	E_{ts}	V_{CC} = 600 V, V_{GE} = 0/15 V, $R_{G(on)}$ = 8 Ω, $R_{G(off)}$ = 8 Ω	T_{vj} = 25 °C, I_C = 50 A		2.45		mJ
			T_{vj} = 175 °C, I_C = 50 A		4.58		
Operating junction temperature	T_{vj}			-40		175	°C

Note: Electrical Characteristic, at T_{vj} = 25°C, unless otherwise specified.

3 Diode

Table 4 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Diode forward current, limited by T_{vjmax}	I_F		T_c = 25 °C	81	A
			T_c = 100 °C	51	
Diode pulsed current, t_p limited by T_{vjmax}	I_{Fpulse}			200	A
Power dissipation	P_{tot}		T_c = 25 °C	232	W
			T_c = 100 °C	115	

Table 5 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Diode forward voltage	V_F	I_F = 50 A	T_{vj} = 25 °C		2.5	3	V
			T_{vj} = 175 °C		2.3		
Diode reverse recovery time	t_{rr}	V_R = 600 V, $R_{G(on)}$ = 8 Ω	T_{vj} = 25 °C, I_F = 50 A		96		ns
			T_{vj} = 175 °C, I_F = 50 A		168		
Diode reverse recovery charge	Q_{rr}	V_R = 600 V, $R_{G(on)}$ = 8 Ω	T_{vj} = 25 °C, I_F = 50 A		1.74		µC
			T_{vj} = 175 °C, I_F = 50 A		4.63		

(table continues...)

Table 5 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Diode peak reverse recovery current	I_{rrm}	V_R = 600 V, $R_{G(on)}$ = 8 Ω	T_{vj} = 25 °C, I_F = 50 A		58		A
			T_{vj} = 175 °C, I_F = 50 A		95		
Diode peak rate of fall of reverse recovery current	di_{rr}/dt	V_R = 600 V, $R_{G(on)}$ = 8 Ω	T_{vj} = 25 °C, I_F = 50 A		-1830		A/µs
			T_{vj} = 150 °C, I_F = 50 A		-2520		
Reverse recovery energy	E_{rec}	V_R = 600 V, $R_{G(on)}$ = 8 Ω	T_{vj} = 25 °C, I_F = 50 A		0.72		mJ
			T_{vj} = 175 °C, I_F = 50 A		1.86		
Operating junction temperature	T_{vj}			-40		175	°C

Note: *For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.*

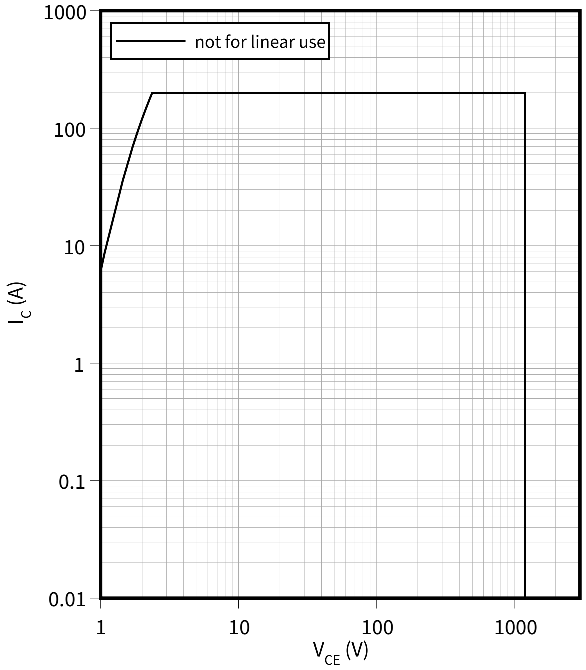
Dynamic test circuit, parasitic inductance L_σ = 30 nH, C_σ = 18 pF

4 Characteristics diagrams

Reverse bias safe operating area

$I_C = f(V_{CE})$

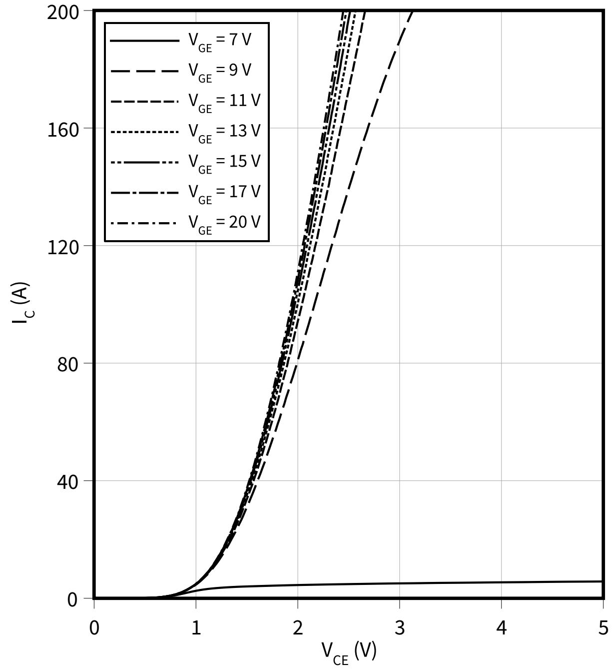
$T_{vj} \leq 175\ °C$, $V_{GE} = 0/15\ V$



Typical output characteristic

$I_C = f(V_{CE})$

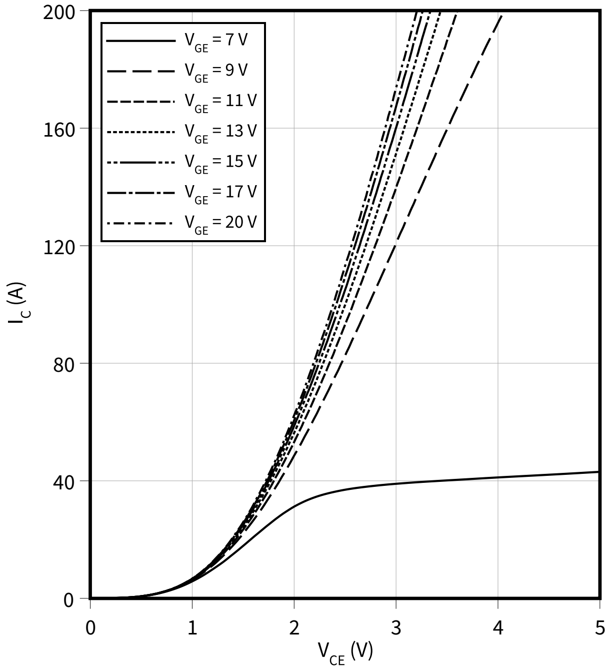
$T_{vj} = 25\ °C$



Typical output characteristic

$I_C = f(V_{CE})$

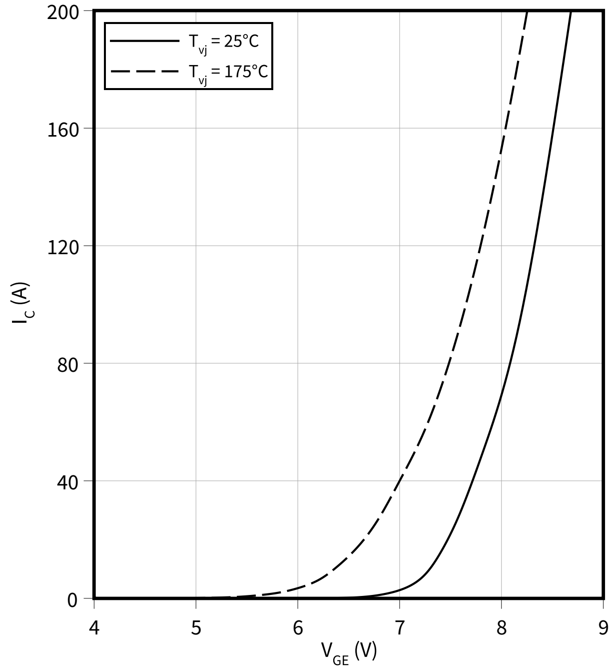
$T_{vj} = 175\ °C$



Typical transfer characteristic

$I_C = f(V_{GE})$

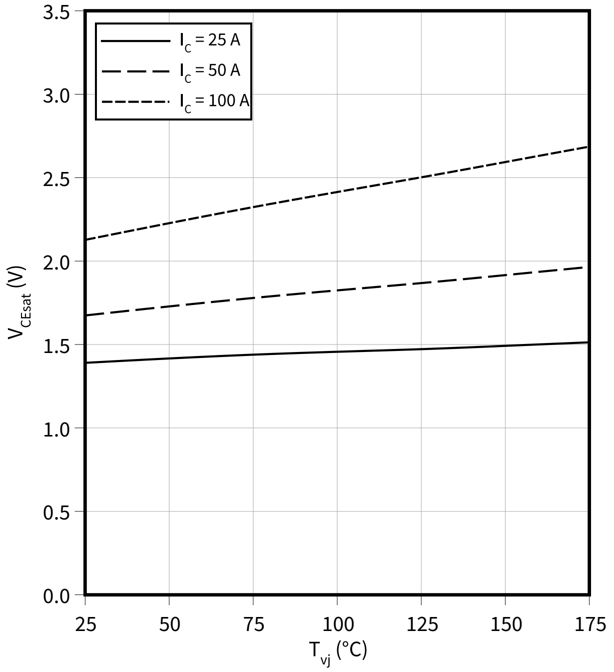
$V_{CE} = 20\ V$



Typical collector-emitter saturation voltage as a function of junction temperature

$V_{CEsat} = f(T_{vj})$

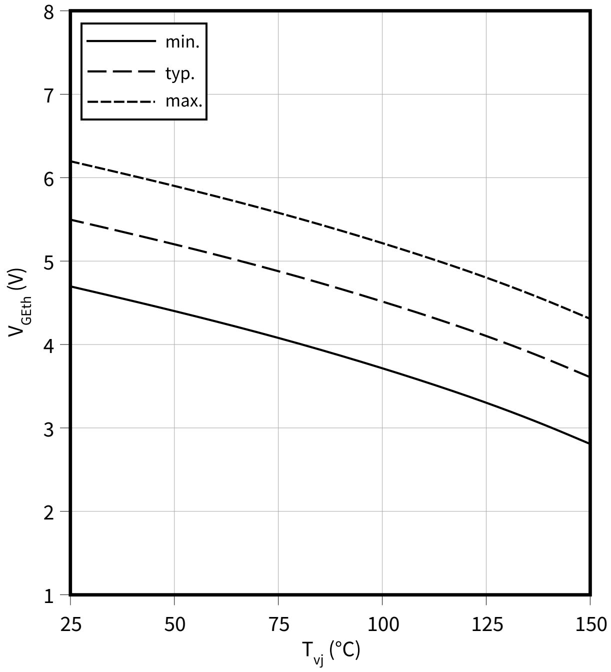
$V_{GE} = 15\ V$



Gate-emitter threshold voltage as a function of junction temperature

$V_{GEth} = f(T_{vj})$

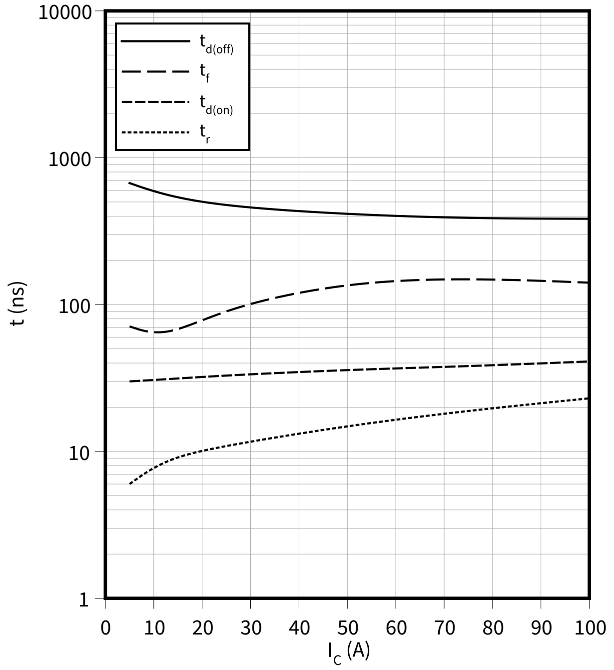
$I_C = 0.8\ mA$



Typical switching times as a function of collector current

$t = f(I_C)$

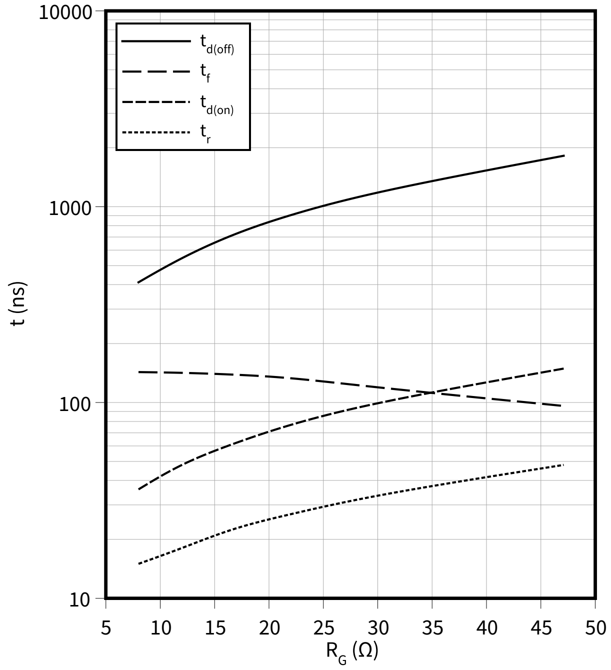
$T_{vj} = 175\ °C, V_{GE} = 0/15\ V, V_{CC} = 600\ V, R_G = 8\ \Omega$



Typical switching times as a function of gate resistor

$t = f(R_G)$

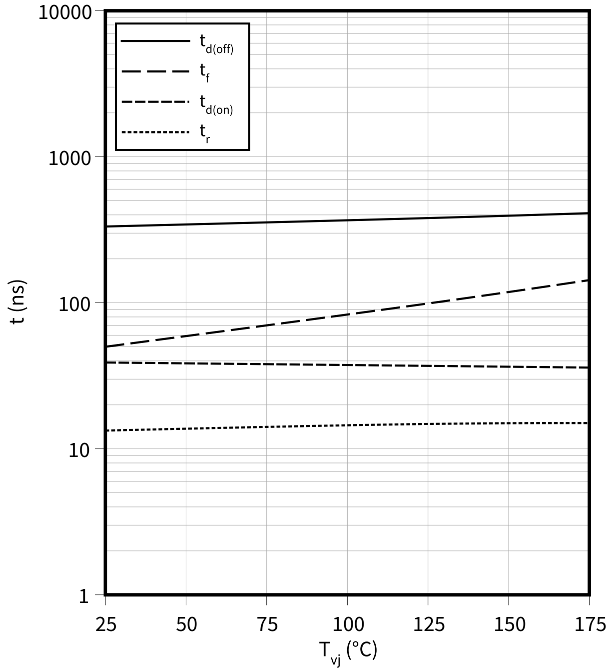
$I_C = 50\ A, V_{CC} = 600\ V, T_{vj} = 175\ °C, V_{GE} = 0/15\ V$



Typical switching times as a function of junction temperature

$t = f(T_{vj})$

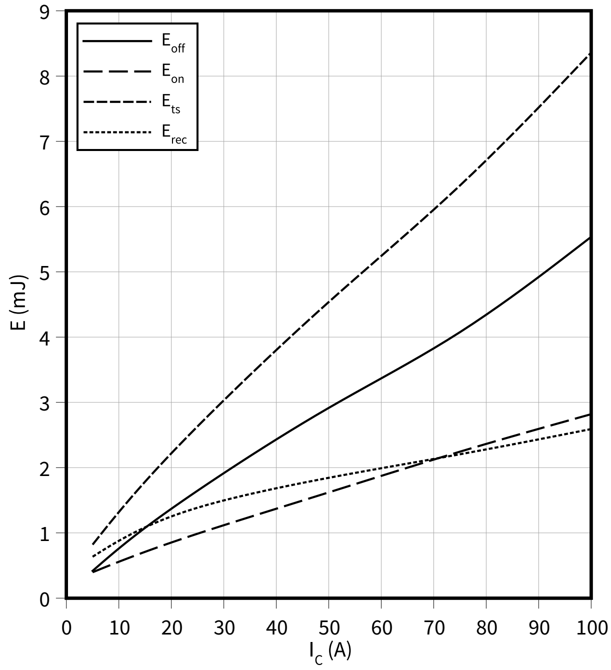
$I_C = 50$ A, $V_{CC} = 600$ V, $V_{GE} = 0/15$ V, $R_G = 8\ \Omega$



Typical switching energy losses as a function of collector current

$E = f(I_C)$

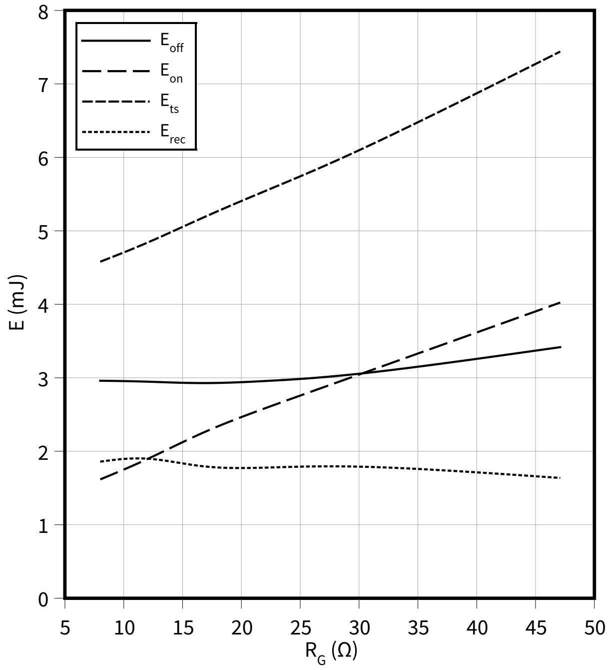
$V_{CC} = 600$ V, $T_{vj} = 175$ °C, $V_{GE} = 0/15$ V, $R_G = 8\ \Omega$



Typical switching energy losses as a function of gate resistor

$E = f(R_G)$

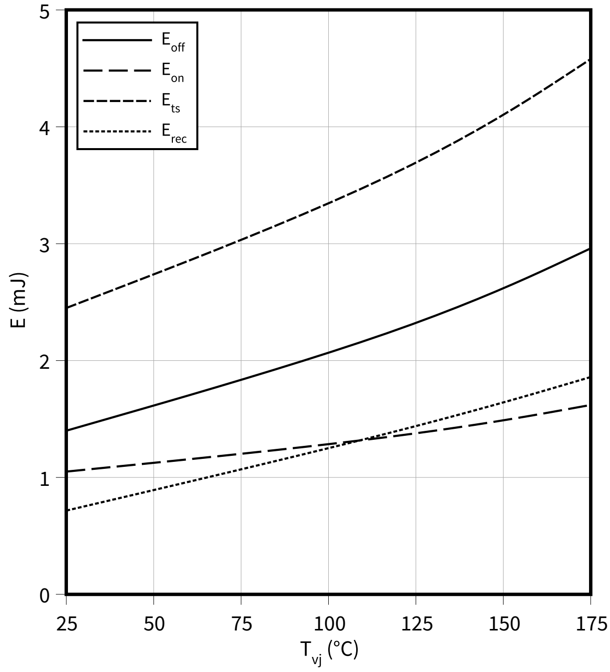
$I_C = 50$ A, $V_{CC} = 600$ V, $T_{vj} = 175$ °C, $V_{GE} = 0/15$ V



Typical switching energy losses as a function of junction temperature

$E = f(T_{vj})$

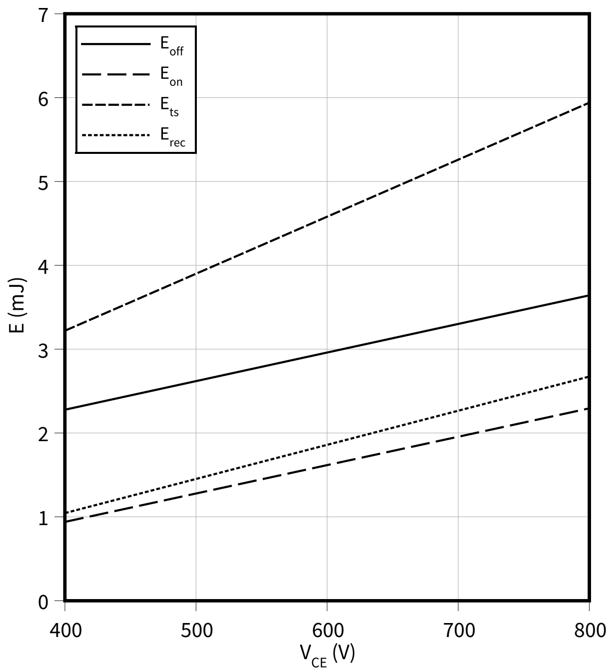
$I_C = 50$ A, $V_{CC} = 600$ V, $V_{GE} = 0/15$ V, $R_G = 8\ \Omega$



Typical switching energy losses as a function of collector emitter voltage

$E = f(V_{CE})$

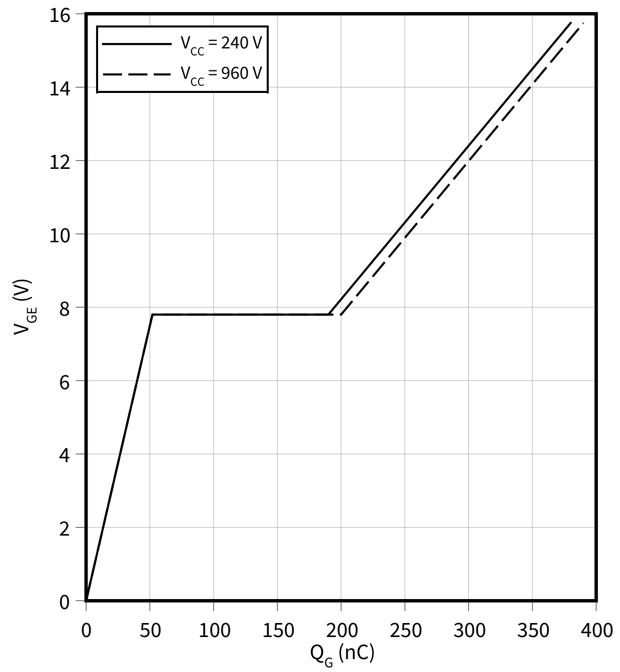
$I_C = 50$ A, $T_{vj} = 175$ °C, $V_{GE} = 0/15$ V, $R_G = 8\ \Omega$



Typical gate charge

$V_{GE} = f(Q_G)$

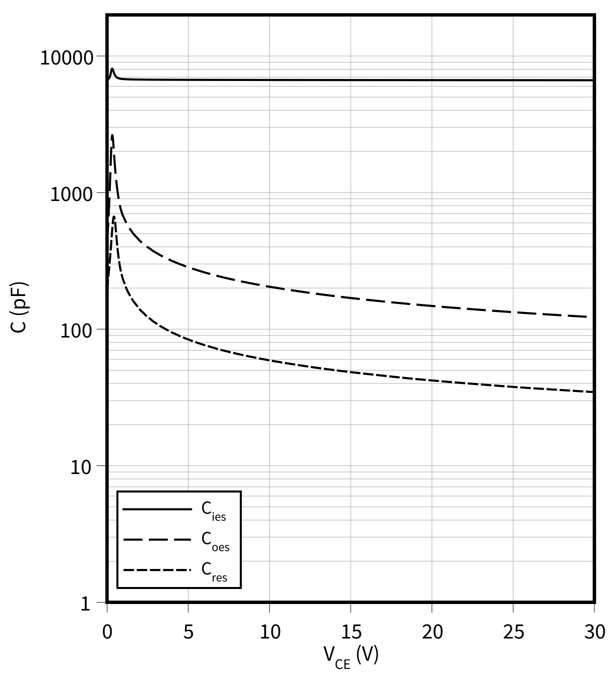
$I_C = 50$ A



Typical capacitance as a function of collector-emitter voltage

$C = f(V_{CE})$

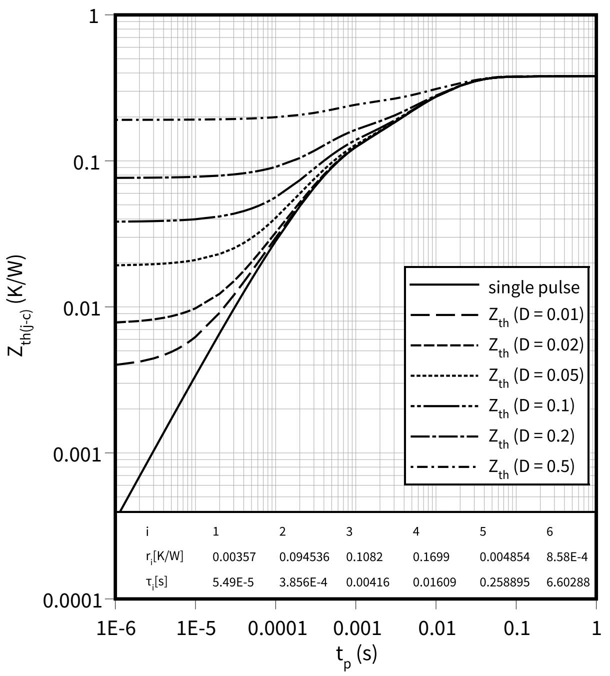
$f = 100$ kHz, $V_{GE} = 0$ V



IGBT transient thermal impedance as a function of pulse width

$Z_{th(j-c)} = f(t_p)$

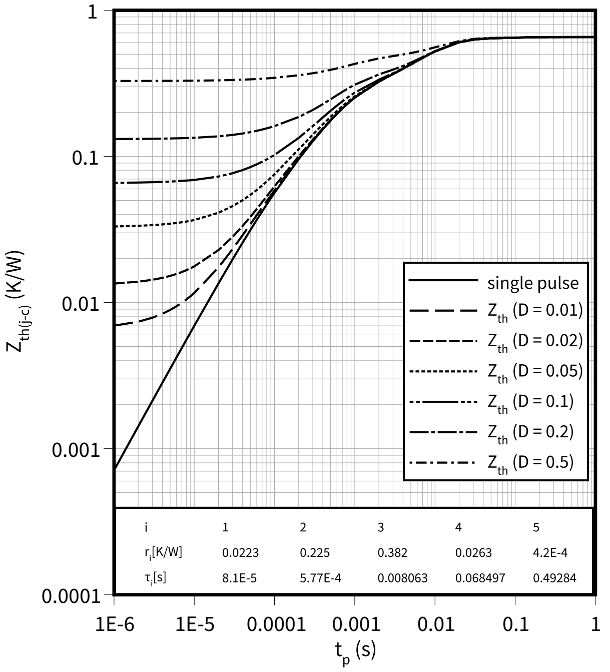
$D = t_p/T$



Diode transient thermal impedance as a function of pulse width

$Z_{th(j-c)} = f(t_p)$

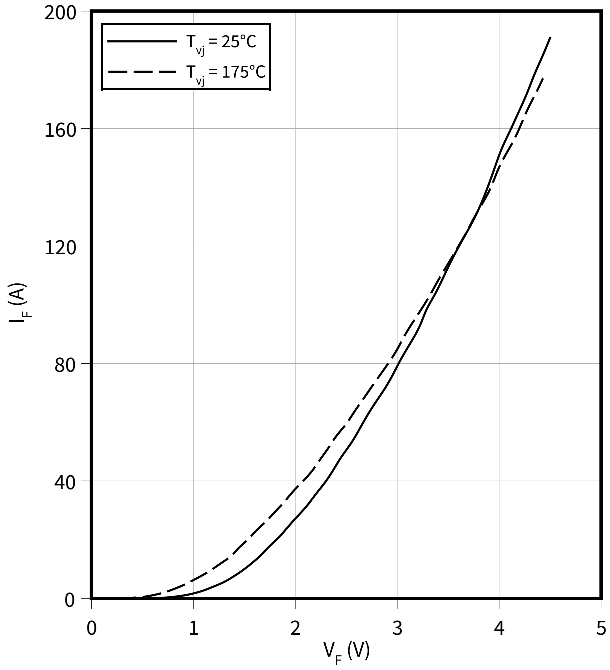
$D = t_p/T$



i	1	2	3	4	5
r_i[K/W]	0.0223	0.225	0.382	0.0263	4.2E-4
τ_i[s]	8.1E-5	5.77E-4	0.008063	0.068497	0.49284

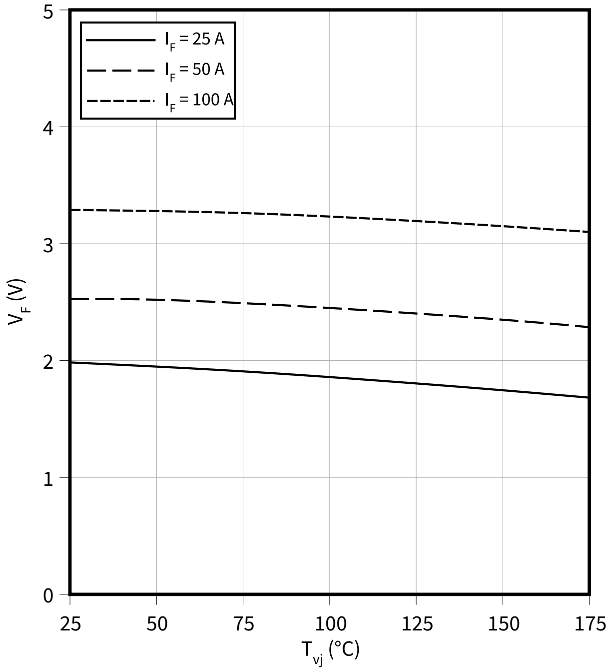
Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$



Typical diode forward voltage as a function of junction temperature

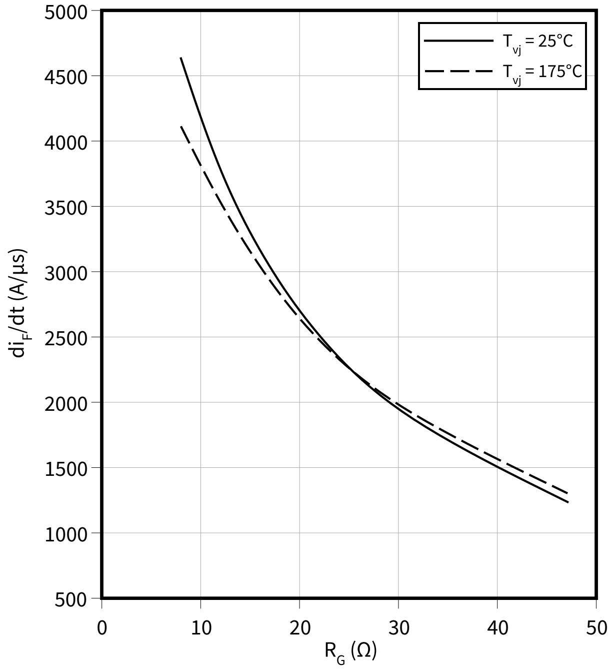
$V_F = f(T_{vj})$



Typical diode current slope as a function of gate resistor

$di_F/dt = f(R_G)$

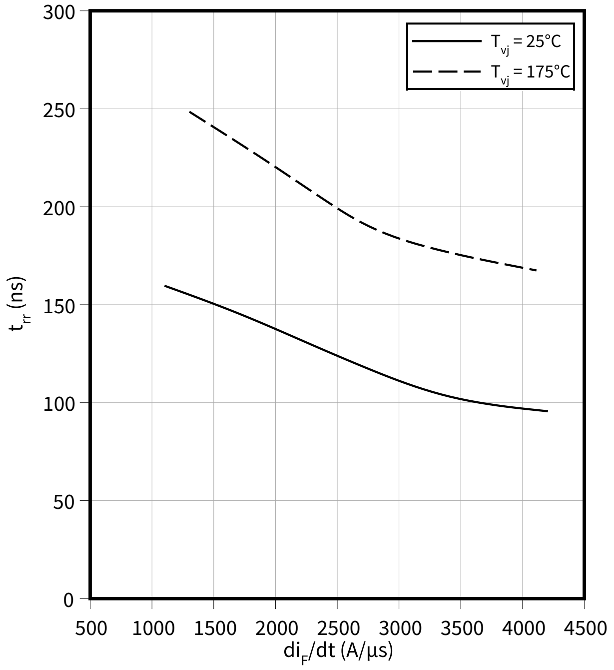
$V_R = 600$ V, $I_F = 50$ A



Typical reverse recovery time as a function of diode current slope

$t_{rr} = f(di_F/dt)$

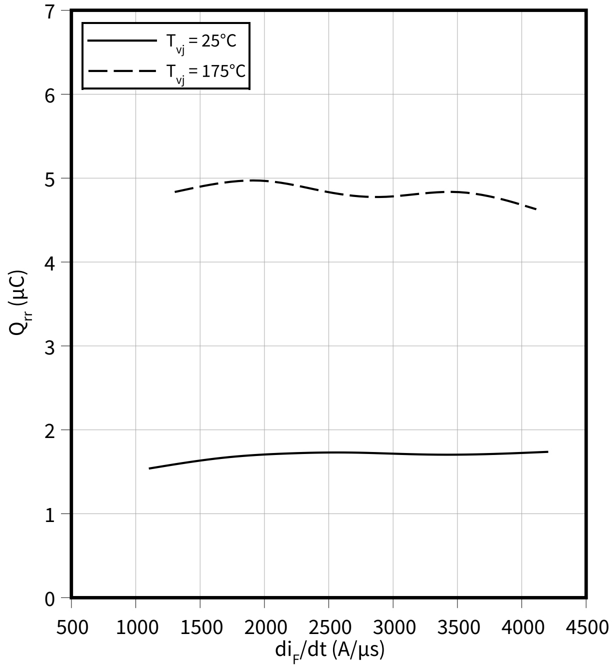
$V_R = 600$ V, $I_F = 50$ A



Typical reverse recovery charge as a function of diode current slope

$Q_{rr} = f(di_F/dt)$

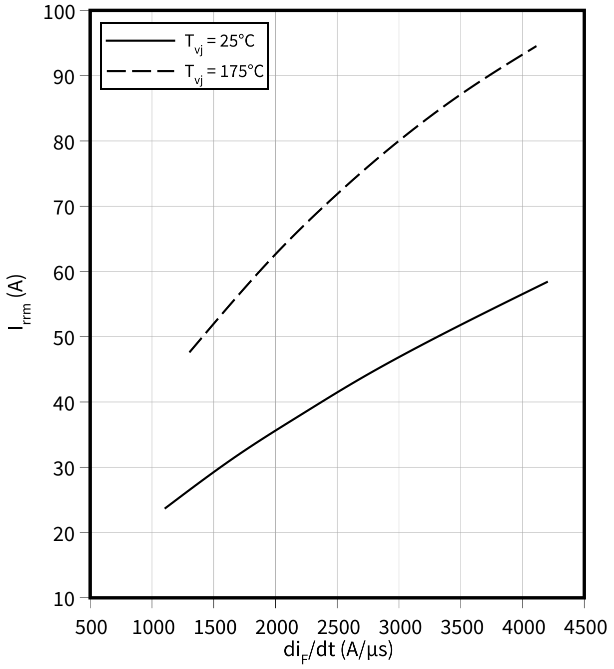
$V_R = 600$ V, $I_F = 50$ A



Typical reverse recovery current as a function of diode current slope

$I_{rrm} = f(di_F/dt)$

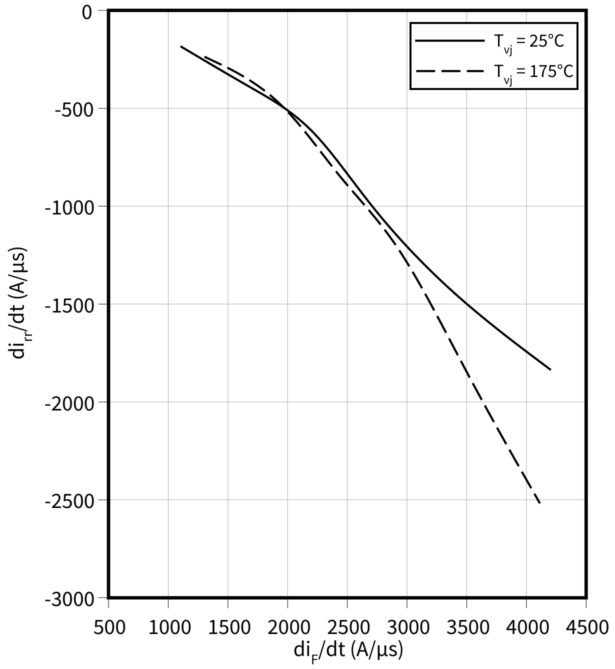
$V_R = 600$ V, $I_F = 50$ A



Typical diode peak rate of fall of reverse recovery current as a function of diode current slope

$di_{rr}/dt = f(di_F/dt)$

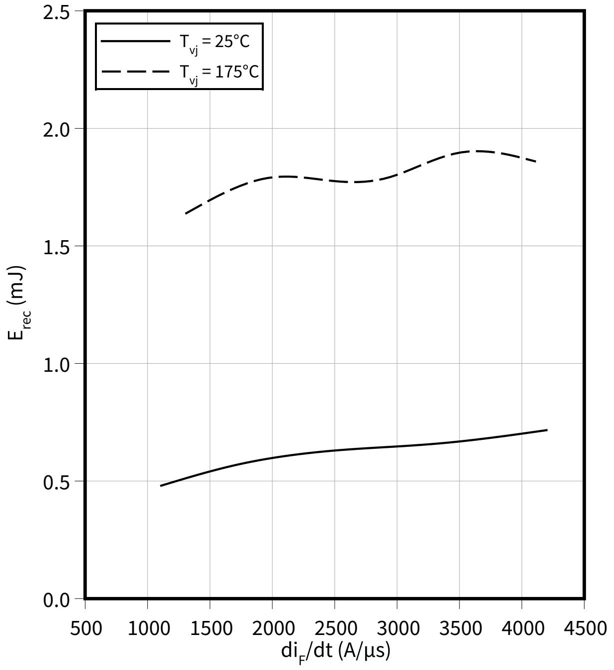
$V_R = 600$ V, $I_F = 50$ A



Typical reverse energy losses as a function of diode current slope

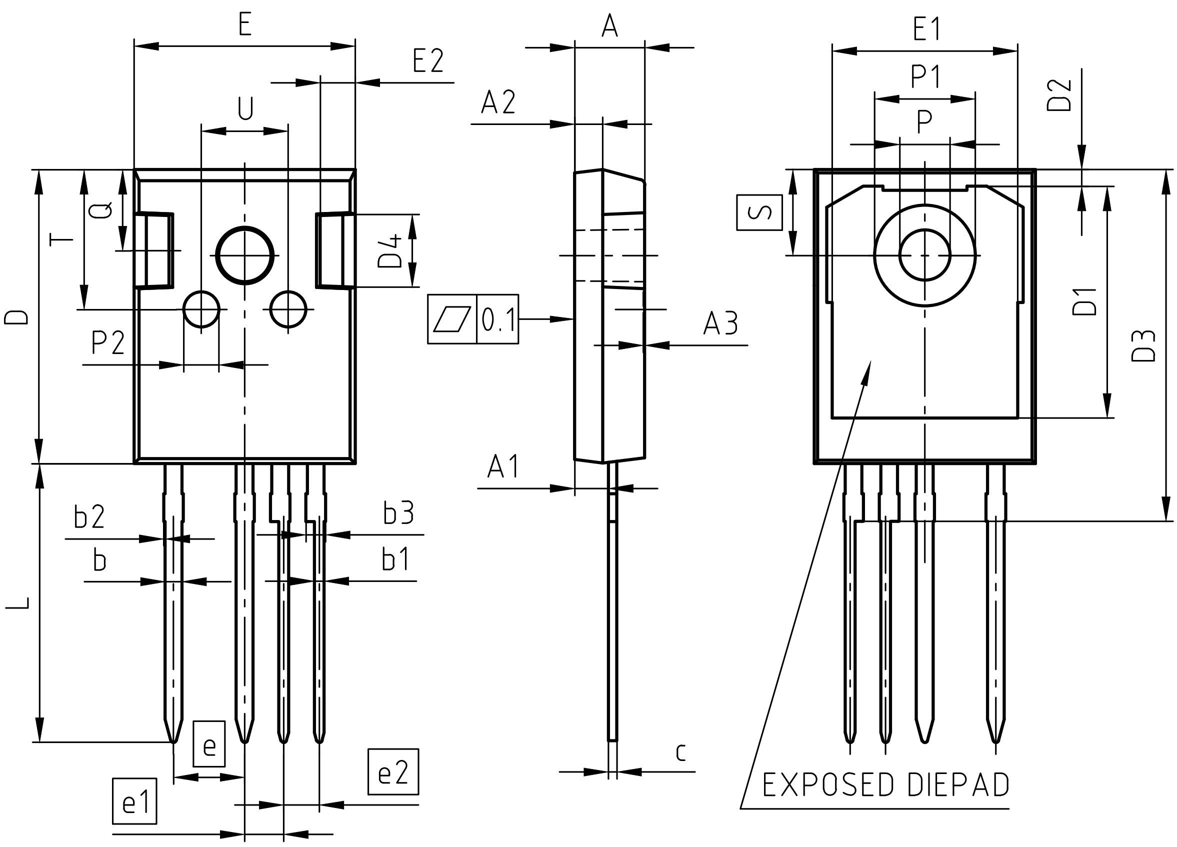
$E_{rec} = f(di_F/dt)$

$V_R = 600$ V, $I_F = 50$ A



5 Package outlines

PG-TO247-4-STD-NT3.7



NOTES:
ALL DIMENSIONS DO NOT INCLUDE MOLD FLASH
OR PROTRUSIONS.

PACKAGE - GROUP NUMBER:	PG-TO247-4-U02				
DIMENSIONS	MILLIMETERS		DIMENSIONS	MILLIMETERS	
	MIN.	MAX.		MIN.	MAX.
A	4.90	5.10	E	15.70	15.90
A1	2.31	2.51	E1	13.10	13.50
A2	1.90	2.10	E2	2.40	2.60
A3	0.05	0.25	e	5.08	
b	1.10	1.30	e1	2.79	
b1	0.65	0.79	e2	2.54	
b2	---	0.20	N	4	
b3	1.34	1.44	L	19.80	20.10
c	0.58	0.66	øP	3.50	3.70
D	20.90	21.10	øP1	7.00	7.40
D1	16.25	16.85	øP2	2.40	2.60
D2	1.05	1.35	Q	5.60	6.00
D3	24.97	25.27	S	6.15	
D4	4.90	5.10	T	9.80	10.20
			U	6.00	6.40

Figure 1

6 Testing conditions

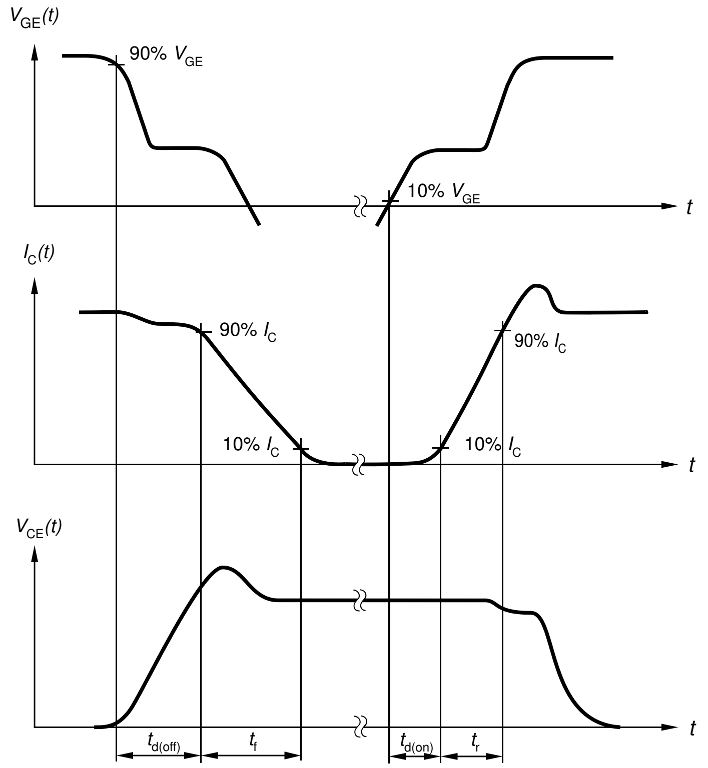


Figure A. **Definition of switching times**

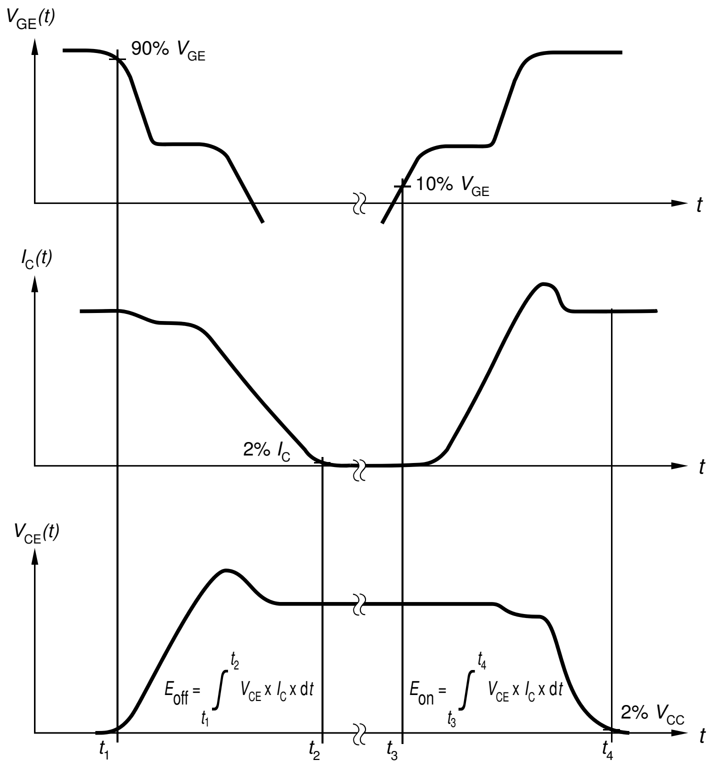


Figure B. **Definition of switching losses**

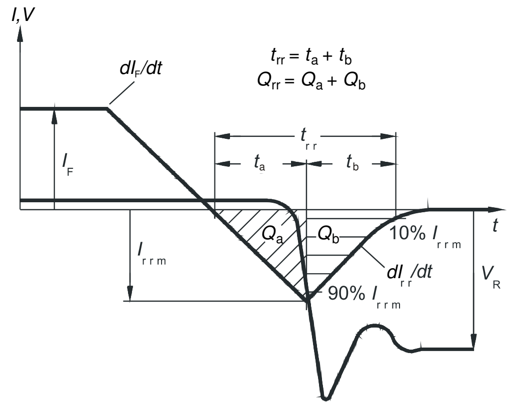


Figure C. **Definition of diode switching characteristics**

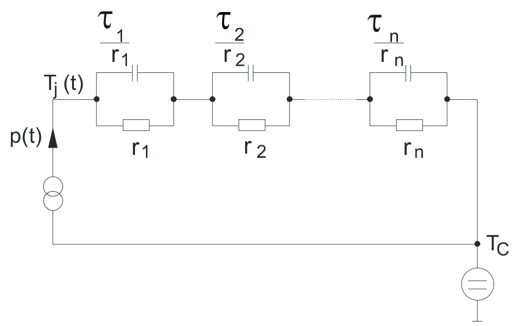


Figure D. **Thermal equivalent circuit**

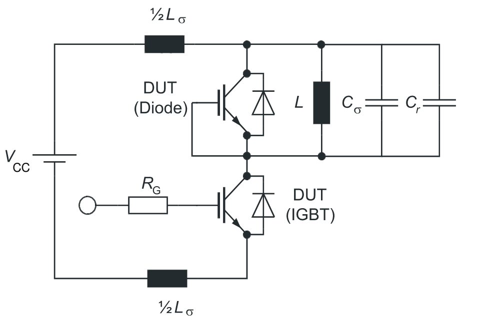


Figure E. **Dynamic test circuit**
Parasitic inductance L_{σ},
parasitic capacitor C_{σ},
relief capacitor C_r,
(only for ZVT switching)

Figure 2

Revision history

Document revision	Date of release	Description of changes
0.10	2022-05-02	Target datasheet
0.20	2022-06-01	Editorial changes
1.00	2022-11-09	Final datasheet
1.10	2022-11-23	Update of potential applications
1.20	2023-01-19	Correction of E_{on} at 25°C on page 4 Adaption of graph $E = f(T_{vj})$ on page 9

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